

In the Specification:

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The FIB used in the preferred embodiment uses Ga ions. To avoid Ga beam damage during FIB platinum deposition, a thin oxide layer is deposited in a plasma enhanced CVD chamber (**Step 1**). In the preferred embodiment, silicon oxide is deposited to a thickness of approximately 180 nm at the center of the wafer. Depositing the oxide on the entire wafer takes approximately 5 minutes. The wafer is then cleaved to separate a piece from an area of interest for sampling (**Step 2**). The sample to be analyzed is then placed in a dual beam FIB machine capable of generating SEM surface imaging and FIB deposition (**Step 3**). The region to be sampled is imaged in SEM mode at adequate magnification. Once the proper area is located, a thin strip box of 80 to 200 nanometers, preferably about 0.13 micrometers wide, 0.6 micrometers tall and 18 micrometers long is drawn over the interested area (**Step 4**). **Figure 2a** shows the sample after **Step 4**. The sample **202** has drawn on it a thin box **204** that will define the mask.